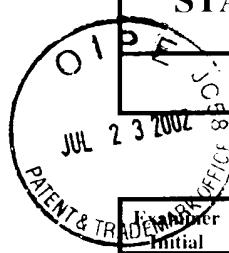


INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: 150.01140101	Serial No.: 10/028,040
	Applicant(s): Sinha et al.	Confirmation No.: 2997
	Filing Date: December 21, 2001	Group: 2812
Information Disclosure Statement mailed:		July 19, 2002

**U.S. PATENT DOCUMENTS**

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
YC	4,992,137	02/12/91	Cathey, Jr. et al.			
	5,254,217	10/19/93	Maniar et al.			
	5,380,401	01/10/95	Jones et al.			
	5,392,189	02/21/95	Fazan et al.			
	5,575,885	11/19/96	Hirabayashi et al.			
	5,692,950	12/02/97	Rutherford et al.			
	5,711,851	01/27/98	Blalock et al.			
	5,786,259	07/28/98	Kang			
	5,888,906	03/30/99	Sandhu et al.			
	5,916,855	06/29/99	Avanzino et al.			
	5,954,997	09/21/99	Kaufman et al.			
	5,976,928	11/02/99	Kirlin et al.			
	5,981,454	11/09/99	Small			
	5,989,988	11/23/99	Iinuma et al.			
	6,039,633	03/21/00	Chopra			
	6,045,716	04/04/00	Walsh et al.			
	6,071,816	06/06/00	Watts et al.			
	6,143,191	11/07/00	Baum et al.			
	6,149,828	11/21/00	Vaartstra			
	6,211,034	04/03/01	Visokay et al.			
	6,290,736 B1	09/18/01	Evans			
	6,346,741 B1	02/12/02	Van Buskirk et al.			
	6,368,518	04/09/02	Vaartstra			
YC	6,395,194 B1	05/28/02	Russell et al.			

EXAMINER

YC

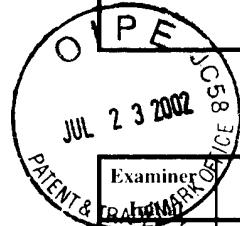
Date Considered

7/17/03

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

RECEIVED
JULY 23 2002
PATENT & TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT	Atty. Docket No.: 150.01140101	Serial No.: 10/028,040
	Applicant(s): Sinha et al.	Confirmation No.: 2997
	Filing Date: December 21, 2001	Group: 2812
P E	Information Disclosure Statement mailed: July <u>19</u> , 2002	



FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
YL	WO 98/06541	02/19/98	PCT				
	WO 98/36045	08/20/98	PCT				
	WO 99/27581	06/03/99	PCT				
	WO 99/53532	10/21/99	PCT				
YL	WO 00/31794	06/02/00	PCT				

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Document Description
YL	Canterford et al., "Chapter 9: Rhodium and Iridium," <i>Halides of the Transition Elements, Halides of the Second and Third Row Transition Metals</i> , John Wiley & Sons, New York, NY, 1968; pgs. 346-357, publication page, title page (14 pages total).
	DeOrnellas et al., "Challenges for Plasma Etch Integration of Ferroelectric Capacitors in FeRAM's and DRAM's," <i>Integrated Ferroelectrics</i> , 1997;17:395-402.
	DeOrnellas et al., "Plasma Etch of Ferroelectric Capacitors in FeRAMs and DRAMs," <i>Semiconductor International</i> , 1997 Sept.; pgs. 103-104, 106 and 108.
	Ginzburg et al., <i>Analytical Chemistry of Platinum Metals</i> , John Wiley & Sons, New York, cover pg., and 14-15.
	Kim et al., "Chemical Dry Etching of Platinum Using Cl ₂ /CO Gas Mixture," <i>Chem. Mater.</i> , 1998;10:3576-3582.
	Kwon et al., "Etching properties of Pt thin films by inductively coupled plasma," <i>J. Vac. Sci. Technol.</i> , 1998;A 16(5):2772-6.
	Nakao, "Dissolution of Noble Metals in Halogen-Halide-Polar Organic Solvent Systems," <i>J. Chem. Soc., Chem. Commun.</i> , 1992 March 1; 5:426-7.
YL	Wilberg, <i>Lehrbuch der Anorganischen Chemie</i> , Walter de Gruyter, Berlin, 1985, Cover pg., and 1188.

EXAMINER <i>YL</i>	Date Considered <i>7/17/05</i>
<p>*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

INFORMATION DISCLOSURE STATEMENT <i>O</i> <i>JUL 23 2002</i> <i>PATENT & TRADEMARK OFFICE 850</i>	Atty. Docket No.: 150.01140101	Serial No.: 10/028,040
	Applicant(s): Sinha et al.	Confirmation No.: 2997
	Filing Date: December 21, 2001	Group: 2812
	Information Disclosure Statement mailed: July <u>19</u> , 2002	

Examiner Initial	Document Description
<i>gc</i>	Xu et al., "Chemical Vapor Deposition (CVD) of Iridium and Platinum Films and Gas-Phase Chemical Etching of Iridium Thin Films," <i>Mat. Res. Soc. Symp. Proc.</i> , 1999;541:129-139.

RECEIVED
JUL 25 2002

RECEIVED
JULY 25 2002
REGISTRATION NUMBER 2806

EXAMINER <i>gc</i>	Date Considered <i>7/17/03</i>
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	